Kaoru Toko

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/4280228/publications.pdf

Version: 2024-02-01

271	5,171	101543	155660
papers	citations	36 h-index	55 g-index

273	273	273	1438
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High-temperature post-annealing effect on the surface morphology and photoresponse and electrical properties of B-doped BaSi2 films grown by molecular beam epitaxy under various Ba-to-Si deposition rate ratios. Journal of Crystal Growth, 2022, 578, 126429.	1.5	7
2	Growth conditions for high-photoresponsivity randomly oriented polycrystalline BaSi₂ films by radio-frequency sputtering: Comparison with BaSi₂ epitaxial films. Applied Physics Express, 2022, 15, 025502.	2.4	6
3	Flexible Thermoelectric Generator Based on Polycrystalline SiGe Thin Films. Materials, 2022, 15, 608.	2.9	6
4	Three-Dimensionally Orientation-Controlled Ge Rods on an Insulator Formed by Low-Temperature Ni-Induced Lateral Crystallization. Crystal Growth and Design, 2022, 22, 1123-1129.	3.0	3
5	Zn_{1â€“x}Ge_xO_y Passivating Interlayers for BaSi₂ Thin-Film Solar Cells. ACS Applied Materials & Interfaces, 2022, 14, 13828-13835.	8.0	10
6	Record-High Hole Mobility Germanium on Flexible Plastic with Controlled Interfacial Reaction. ACS Applied Electronic Materials, 2022, 4, 269-275.	4.3	21
7	High electron mobility in randomly oriented polycrystalline BaSi₂ films formed through radio-frequency sputtering. AIP Advances, 2022, 12, 045120.	1.3	7
8	Machine learning of fake micrographs for automated analysis of crystal growth process. Science and Technology of Advanced Materials Methods, 2022, 2, 213-221.	1.3	3
9	Solid-phase crystallization of gallium arsenide thin films on insulators. Materials Science in Semiconductor Processing, 2021, 124, 105623.	4.0	4
10	Formation of high-photoresponsivity BaSi₂ films on glass substrate by radio-frequency sputtering for solar cell applications. Journal Physics D: Applied Physics, 2021, 54, 135106.	2.8	13
11	Thickness-dependent thermoelectric properties of Si1â^’xGex films formed by Al-induced layer exchange. Journal of Applied Physics, 2021, 129, .	2.5	10
12	Strain effects on polycrystalline germanium thin films. Scientific Reports, 2021, 11, 8333.	3.3	23
13	Comparison of C doping technique between SiC and C targets for high-photoresponsivity BaSi₂ films by radio-frequency sputtering. Japanese Journal of Applied Physics, 2021, 60, 058001.	1.5	5
14	Mechanisms of carrier lifetime enhancement and conductivity-type switching on hydrogen-incorporated arsenic-doped BaSi2. Thin Solid Films, 2021, 724, 138629.	1.8	8
15	Solar cell operation of sputter-deposited n-BaSi₂/p-Si heterojunction diodes and characterization of defects by deep-level transient spectroscopy. Applied Physics Express, 2021, 14, 051010.	2.4	9
16	Grain size dependent photoresponsivity in GaAs films formed on glass with Ge seed layers. Scientific Reports, 2021, 11, 10159.	3.3	2
17	Low-temperature solid-phase crystallization of group IV material thin films. , 2021, , .		0
18	High thermoelectric power factors in polycrystalline germanium thin films. Applied Physics Letters, 2021, 119, .	3.3	10

#	Article	IF	Citations
19	Layer exchange synthesis of multilayer graphene. Nanotechnology, 2021, 32, 472005.	2.6	8
20	Composition dependent properties of p- and n-type polycrystalline group-IV alloy thin films. Journal of Alloys and Compounds, 2021, 887, 161306.	5.5	5
21	Effect of post-annealing on the significant photoresponsivity enhancement of BaSi₂ epitaxial films on Si(111). Applied Physics Express, 2021, 14, 021003.	2.4	8
22	Sn Concentration Effects on Polycrystalline GeSn Thin Film Transistors. IEEE Electron Device Letters, 2021, 42, 1735-1738.	3.9	8
23	Effects of Ba-to-Si deposition rate ratios on the electrical and photoresponse properties of arsenic-doped n-type BaSi2 films. Thin Solid Films, 2021, 738, 138969.	1.8	4
24	Modeling the effects of defect parameters on the performance of a p-BaSi2/n-Si heterojunction solar cell. Solar Energy Materials and Solar Cells, 2020, 205, 110244.	6.2	7
25	Influence of Ba-to-Si deposition rate ratios on the electrical and optical properties of B-doped BaSi2 epitaxial films. Japanese Journal of Applied Physics, 2020, 59, SFFA04.	1.5	7
26	Fe-induced layer exchange of multilayer graphene for rechargeable battery anodes. Applied Physics Express, 2020, 13, 025501.	2.4	6
27	Thin-film thermoelectric generator based on polycrystalline SiGe formed by Ag-induced layer exchange. Applied Physics Letters, 2020, 117, .	3.3	9
28	Multilayer Graphene Battery Anodes on Plastic Sheets for Flexible Electronics. ACS Applied Energy Materials, 2020, 3, 8410-8414.	5.1	10
29	Influence of grain boundaries on the properties of polycrystalline germanium. Journal of Applied Physics, 2020, 128, .	2.5	3
30	Zn-induced layer exchange of p- and n-type nanocrystalline SiGe layers for flexible thermoelectrics. Applied Physics Letters, 2020, 116, .	3.3	13
31	Metal-induced layer exchange of group IV materials. Journal Physics D: Applied Physics, 2020, 53, 373002.	2.8	50
32	Drastic enhancement of photoresponsivity in C-doped BaSi2 films formed by radio-frequency sputtering. Japanese Journal of Applied Physics, 2020, 59, SFFA06.	1.5	6
33	Effects of sputtering pressure and temperature of ITO electrodes on the performance of p-BaSi₂/n-Si heterojunction solar cells. Japanese Journal of Applied Physics, 2020, 59, SFFA07.	1.5	0
34	Significant enhancement of photoresponsivity in As-doped n-BaSi₂epitaxial films by atomic hydrogen passivation. Applied Physics Express, 2020, 13, 051001.	2.4	8
35	Effects of boron and hydrogen doping on the enhancement of photoresponsivity and photoluminescence of BaSi₂ epitaxial films. Japanese Journal of Applied Physics, 2020, 59, SFFA08.	1.5	5
36	Fabrication of As-doped n-type BaSi2 epitaxial films grown by molecular beam epitaxy. Japanese Journal of Applied Physics, 2020, 59, SFFA01.	1.5	7

#	Article	IF	Citations
37	Atomic hydrogen passivation for photoresponsivity enhancement of boron-doped p-BaSi2 films and performance improvement of boron-doped p-BaSi2/n-Si heterojunction solar cells. Journal of Applied Physics, 2020, 127, .	2.5	13
38	Strong correlation between uniaxial magnetic anisotropic constant and in-plane tensile strain in Mn4N epitaxial films. AIP Advances, 2020, 10, .	1.3	27
39	Manipulation of saturation magnetization and perpendicular magnetic anisotropy in epitaxial <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi mathvariant="normal">C</mml:mi><mml:msub><mml:mi mathvariant="normal">o</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:mi mathvariant="normal">M</mml:mi><mml:msub><mml:mi mathvariant="normal">n</mml:mi><mml:mrow><mml:mn>4</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi></mml:mrow></	3.2	18
40	Perpendicular magnetic anisotropy in ferrimagnetic Mn4N films grown on (LaAlO3)0.3(Sr2TaAlO6)0.7(0Â0Â1) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2020, 535, 125566.	1.5	12
41	Improving photoresponsivity in GaAs film grown on Al-induced-crystallized Ge on an insulator. AIP Advances, 2020, 10, 015153.	1.3	3
42	Fabrication of high-photoresponsivity BaSi₂films formed on conductive layers by radio-frequency sputtering. Applied Physics Express, 2020, 13, 075506.	2.4	3
43	Improved thermoelectric performance of flexible p-type SiGe films by B-doped Al-induced layer exchange. Journal Physics D: Applied Physics, 2020, 53, 075105.	2.8	8
44	Magnetic reversal in rare-earth free Mn4â€‰â^’â€‰xNixN epitaxial films below and above Ni composition needed for magnetic compensation around room temperature. Journal of Applied Physics, 2020, 127, .	2.5	23
45	Impact of the carbon membrane inserted below Ni in the layer exchange of multilayer graphene. CrystEngComm, 2020, 22, 3106-3109.	2.6	1
46	350 Â°C synthesis of high-quality multilayer graphene on an insulator using Ni-induced layer exchange. Applied Physics Express, 2020, 13, 055502.	2.4	19
47	Impact of radio-frequency power on the photoresponsivity enhancement of BaSi₂ films formed by sputtering. Applied Physics Express, 2020, 13, 085511.	2.4	8
48	Four-step heating process for solid-phase crystallization of Ge leading to high carrier mobility. Applied Physics Express, 2020, 13, 101005.	2.4	2
49	Magnetic compensation at two different composition ratios in rare-earth-free <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Mn</mml:mi><mml:mrow><mml:mn>4</mml:mn></mml:mrow></mml:msub><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> ferrimagnetic films. Physical Review Materials, 2020, 4, .	2.4	17
50	Effects of molecular beam epitaxy growth conditions on grain size and lattice strain in a-axis-oriented BaSi₂ films. Japanese Journal of Applied Physics, 2020, 59, SFFA09.	1.5	3
51	Impact of Amorphous-C/Ni Multilayers on Ni-Induced Layer Exchange for Multilayer Graphene on Insulators. ACS Omega, 2019, 4, 14251-14254.	3.5	7
52	Investigation of defect levels in BaSi₂ epitaxial films by photoluminescence and the effect of atomic hydrogen passivation. Journal of Physics Communications, 2019, 3, 075005.	1.2	13
53	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. Applied Physics Letters, 2019, 114, .	3.3	28
54	Correlation of native defects between epitaxial films and polycrystalline BaSi₂ bulks based on photoluminescence spectra. Applied Physics Express, 2019, 12, 111001.	2.4	7

#	Article	IF	Citations
55	Impact of deposition pressure and two-step growth technique on the photoresponsivity enhancement of polycrystalline BaSi₂ films formed by sputtering. Applied Physics Express, 2019, 12, 021004.	2.4	11
56	Magnetic and magneto-transport properties of Mn4N thin films by Ni substitution and their possibility of magnetic compensation. Journal of Applied Physics, 2019, 125, .	2.5	27
57	Investigation of native defects in BaSi₂ epitaxial films by electron paramagnetic resonance. Applied Physics Express, 2019, 12, 061005.	2.4	8
58	80 Â°C synthesis of thermoelectric nanocrystalline Ge film on flexible plastic substrate by Zn-induced layer exchange. Applied Physics Express, 2019, 12, 055501.	2.4	17
59	Minority carrier lifetime of Ge film epitaxial grown on a large-grain seed layer on glass. Thin Solid Films, 2019, 681, 98-102.	1.8	3
60	Solid-phase crystallization of densified amorphous GeSn leading to high hole mobility (540â€‰cm2/V s). Applied Physics Letters, 2019, 114, .	3.3	15
61	Operation of BaSi₂ homojunction solar cells on p⁺-Si(111) substrates and the effect of structure parameters on their performance. Applied Physics Express, 2019, 12, 041005.	2.4	47
62	High-Electrical-Conductivity Multilayer Graphene Formed by Layer Exchange with Controlled Thickness and Interlayer. Scientific Reports, 2019, 9, 4068.	3.3	89
63	High photoresponsivity in a GaAs film synthesized on glass using a pseudo-single-crystal Ge seed layer. Applied Physics Letters, 2019, 114, .	3.3	10
64	Low-Temperature (400 Â°C) Synthesis of Multilayer Graphene by Metal-Assisted Sputtering Deposition. ACS Omega, 2019, 4, 6677-6680.	3.5	19
65	Sb-doped crystallization of densified precursor for n-type polycrystalline Ge on an insulator with high carrier mobility. Applied Physics Letters, 2019, 114, .	3.3	19
66	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi₂ films by Raman spectroscopy. Applied Physics Express, 2019, 12, 055506.	2.4	30
67	Expansion of Solid-phase Interactions between Carbon and Metals: Layer Exchange for Multilayer Graphene on Insulator. , 2019, , .		0
68	Significant improvement on electrical properties of BaSi2 due to atomic H passivation by radio-frequency plasma. , 2019, , .		0
69	High-electron-mobility (370â€‰cm2/Vs) polycrystalline Ge on an insulator formed by As-doped solid-phase crystallization. Scientific Reports, 2019, 9, 16558.	3.3	22
70	Three-step growth of highly photoresponsive BaSi2 light absorbing layers with uniform Ba to Si atomic ratios. Journal of Applied Physics, 2019, 126, .	2.5	16
71	High hole mobility (â‰¥500 cm² V^{â^'1} s^{â^'1}) polycrystalline Ge films on GeO₂-coated glass and plastic substrates. Applied Physics Express, 2019, 12, 015508.	2.4	25
72	Molecular beam epitaxy growth of Mn4â^'Ni N thin films on MgO(0â€¯0â€¯1) substrates and their magnetic properties. Journal of Crystal Growth, 2019, 507, 163-167.	1.5	18

#	Article	IF	Citations
73	Marked enhancement of the photoresponsivity and minority-carrier lifetime of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>BaS</mml:mi><mml:msub><mml:mi mathvariant="normal">i</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> passivated with atomic hydrogen. Physical Review Materials, 2019, 3, .	2.4	20
74	Epitaxial growth and magnetic properties of Fe 4â^' x Mn x N thin films grown on MgO(0â€¯0â€¯1) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2018, 489, 20-23.	1.5	21
75	Impact of Ba to Si deposition rate ratios during molecular beam epitaxy on carrier concentration and spectral response of BaSi2 epitaxial films. Journal of Applied Physics, 2018, 123, 045703.	2.5	55
76	Advanced solid-phase crystallization for high-hole mobility (450) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 627 Td (cm²V<sup> 2018, 11, 031302.	2.4	23
77	Reduction in interface defect density in p-BaSi₂/n-Si heterojunction solar cells by a modified pretreatment of the Si substrate. Japanese Journal of Applied Physics, 2018, 57, 025501.	1.5	11
78	Structural characterization and magnetic properties of L10-MnAl films grown on different underlayers by molecular beam epitaxy. Journal of Crystal Growth, 2018, 486, 19-23.	1.5	4
79	Decrease in electrical contact resistance of Sb-doped n⁺-BaSi₂layers and spectral response of an Sb-doped n⁺-BaSi₂/undoped BaSi₂structure for solar cells. Japanese Journal of Applied Physics, 2018, 57, 031202.	1.5	3
80	Investigation of electrically active defects in undoped BaSi2 light absorber layers using deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2018, 57, 075801.	1.5	12
81	Spectroscopic evidence of photogenerated carrier separation by built-in electric field in Sb-doped n-BaSi₂/B-doped p-BaSi₂homojunction diodes. Japanese Journal of Applied Physics, 2018, 57, 050310.	1.5	26
82	Demonstration of BaSi <inf>2</inf> pn homojunction solar cells and improvement of photoresponsivity of BaSi <inf>2</inf> absorbers by Ba/Si deposition rate ratio. , 2018, , .		0
83	Photoresponsivity improvement of BaSi<inf>2</inf> epitaxial films by capping with hydrogenated amorphous Si layers by radio-frequency<inf>2</inf> plasma. , 2018, , .		0
84	Millimeter-sized magnetic domains in perpendicularly magnetized ferrimagnetic Mn₄N thin films grown on SrTiO₃. Japanese Journal of Applied Physics, 2018, 57, 120310.	1.5	27
85	Metal Catalysts for Layer-Exchange Growth of Multilayer Graphene. ACS Applied Materials & Interfaces, 2018, 10, 41664-41669.	8.0	23
86	Deep level transient spectroscopy characterization of BaSi<inf>2</inf> light absorbers. , 2018, , .		0
87	Significant photoresponsivity enhancement of polycrystalline BaSi₂ films formed on heated Si(111) substrates by sputtering. Applied Physics Express, 2018, 11, 071401.	2.4	20
88	Investigation of p-BaSi<inf>2</inf>/n-Si heterojunction solar cells on Si(001) and comparison to those on Si(111). , 2018, , .		0
89	Improving carrier mobility of polycrystalline Ge by Sn doping. Scientific Reports, 2018, 8, 14832.	3.3	51
90	Improving the photoresponse spectra of BaSi2 layers by capping with hydrogenated amorphous Si layers prepared by radio-frequency hydrogen plasma. AIP Advances, 2018, 8, 055306.	1.3	10

#	Article	IF	Citations
91	Effect of BaSi₂template growth duration on the generation of defects and performance of p-BaSi₂/n-Si heterojunction solar cells. Japanese Journal of Applied Physics, 2018, 57, 042301.	1.5	8
92	High-hole mobility Si1-Ge (0.1 â‰ x â‰ 1) on an insulator formed by advanced solid-phase crystallization. Journal of Alloys and Compounds, 2018, 766, 417-420.	5.5	13
93	p-BaSi2/n-Si heterojunction solar cells on Si(001) with conversion efficiency approaching 10%: comparison with Si(111). Applied Physics Express, 2018, 11, 062301.	2.4	42
94	Detection of local vibrational modes induced by intrinsic defects in undoped BaSi2 light absorber layers using Raman spectroscopy. Journal of Applied Physics, 2018, 124, 025301.	2.5	20
95	Fabrication of SrGe2 thin films on Ge (100), (110), and (111) substrates. Nanoscale Research Letters, 2018, 13, 22.	5.7	1
96	Direct synthesis of multilayer graphene on an insulator by Ni-induced layer exchange growth of amorphous carbon. Applied Physics Letters, 2017, 110, .	3.3	26
97	Highly oriented epitaxial (Î±â€²â€²+Î±â€²)-Fe16N2 films on Î±-Fe(001) buffered MgAl2O4(001) substrates and their magnetization. Journal of Crystal Growth, 2017, 468, 691-695.	1.5	4
98	Effects of Al grain size on metal-induced layer exchange growth of amorphous Ge thin film on glass substrate. Thin Solid Films, 2017, 626, 190-193.	1.8	7
99	Control of grain size and crystallinity of poly-Si films on quartz by Al-induced crystallization. CrystEngComm, 2017, 19, 2305-2311.	2.6	23
100	Fabrication and characterizations of nitrogen-doped BaSi2 epitaxial films grown by molecular beam epitaxy. Journal of Crystal Growth, 2017, 471, 37-41.	1.5	0
101	Effect of p-BaSi₂layer thickness on the solar cell performance of p-BaSi₂/n-Si heterojunction solar cells. Japanese Journal of Applied Physics, 2017, 56, 05DB03.	1.5	19
102	Boron-doped p-BaSi2/n-Si solar cells formed on textured n-Si(0 0 1) with a pyramid structure consisting of {1 1 1} facets. Journal of Crystal Growth, 2017, 475, 186-191.	1.5	9
103	Enhanced spectral response of semiconducting BaSi 2 films by oxygen incorporation. Thin Solid Films, 2017, 629, 17-21.	1.8	14
104	Minority-carrier lifetime and photoresponse properties of B-doped p-BaSi₂, a potential light absorber for solar cells. Japanese Journal of Applied Physics, 2017, 56, 05DB01.	1.5	7
105	Low temperature synthesis of highly oriented p-type Si1-xGex (x: 0â€“1) on an insulator by Al-induced layer exchange. Journal of Applied Physics, 2017, 122, .	2.5	18
106	High-quality multilayer graphene on an insulator formed by diffusion controlled Ni-induced layer exchange. Applied Physics Letters, 2017, 111, .	3.3	26
107	Multilayer graphene on insulator formed by Co-induced layer exchange. Japanese Journal of Applied Physics, 2017, 56, 05DE03.	1.5	10
108	Effect of interlayer on silver-induced layer exchange crystallization of amorphous germanium thin film on insulator. Japanese Journal of Applied Physics, 2017, 56, 05DE04.	1.5	5

#	Article	IF	Citations
109	High-hole mobility polycrystalline Ge on an insulator formed by controlling precursor atomic density for solid-phase crystallization. Scientific Reports, 2017, 7, 16981.	3.3	71
110	Silver-induced layer exchange for polycrystalline germanium on a flexible plastic substrate. Journal of Applied Physics, 2017, 122, .	2.5	16
111	Growth of BaSi2 continuous films on Ge(111) by molecular beam epitaxy and fabrication of p-BaSi2/n-Ge heterojunction solar cells. Japanese Journal of Applied Physics, 2017, 56, 05DB02.	1.5	7
112	Evaluation of band offset at amorphous-Si/BaSi2 interfaces by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2016, 119, .	2.5	32
113	Effect of amorphous Si capping layer on the hole transport properties of BaSi2 and improved conversion efficiency approaching 10% in p-BaSi2/n-Si solar cells. Applied Physics Letters, 2016, 109, .	3.3	109
114	Measurement of valence-band offset at native oxide/BaSi2 interfaces by hard x-ray photoelectron spectroscopy. Journal of Applied Physics, 2016, 119, .	2.5	20
115	Electrical detection of magnetic domain wall in Fe4N nanostrip by negative anisotropic magnetoresistance effect. Journal of Applied Physics, 2016, 120, .	2.5	1
116	p-BaSi2/n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. Applied Physics Letters, 2016, 108, .	3.3	69
117	Influence of air exposure duration and a-Si capping layer thickness on the performance of p-BaSi2/n-Si heterojunction solar cells. AIP Advances, 2016, 6, .	1.3	40
118	Epitaxial growth and magnetic properties of NixFe4-xN (xâ€‰=â€‰0, 1, 3, and 4) films on SrTiO3(001) substrates. Journal of Applied Physics, 2016, 120, .	2.5	16
119	Band alignments at native oxide/BaSi<inf>2</inf> and amorphous-Si/BaSi<inf>2</inf> interfaces measured by hard x-ray photoelectron spectroscopy. , 2016, , .		0
120	Sn-inserted Al-induced layer exchange for large-grained GeSn thin films on insulator. Thin Solid Films, 2016, 616, 316-319.	1.8	1
121	Growth and magnetic properties of epitaxial Fe4N films on insulators possessing lattice spacing close to Si(001) plane. Journal of Crystal Growth, 2016, 455, 66-70.	1.5	10
122	Perpendicular magnetic anisotropy in CoxMn4âˆ’xN (x = 0 and 0.2) epitaxial films and possibility of tetragonal Mn4N phase. AIP Advances, 2016, 6, .	1.3	34
123	Orientation control of intermediate-composition SiGe on insulator by low-temperature Al-induced crystallization. Scripta Materialia, 2016, 122, 86-88.	5.2	14
124	Control of electrical properties of BaSi2 thin films by alkali-metal doping using alkali-metal fluorides. Thin Solid Films, 2016, 603, 218-223.	1.8	6
125	Cross-sectional electric field distributions in BaSi2 homo and BaSi2/Si hetero pn junctions. , 2015, , .		1
126	Characterization of defect levels in undoped n-BaSi₂epitaxial films on Si(111) by deep-level transient spectroscopy. Japanese Journal of Applied Physics, 2015, 54, 07JE01.	1.5	11

#	Article	IF	Citations
127	Transfer-free synthesis of highly ordered Ge nanowire arrays on glass substrates. Applied Physics Letters, 2015, 107, 133102.	3.3	6
128	Influence of Substrate on Crystal Orientation of Large-Grained Si Thin Films Formed by Metal-Induced Crystallization. International Journal of Photoenergy, 2015, 2015, 1-7.	2.5	10
129	Control of domain wall position in L-shaped Fe<inf>4</inf>N negatively spin polarized ferromagnetic nanowire. , 2015, , .		0
130	Fabrication and characterization of BaSi2 films on Ge(111) substrates by molecular beam epitaxy. , 2015, , .		1
131	Improved Surface Quality of the Metal-Induced Crystallized Ge Seed Layer and Its Influence on Subsequent Epitaxy. Crystal Growth and Design, 2015, 15, 1535-1539.	3.0	30
132	Fabrication of L-shaped Fe4N ferromagnetic narrow wires and position control of magnetic domain wall with magnetic field. Japanese Journal of Applied Physics, 2015, 54, 028003.	1.5	3
133	Cross-sectional potential profile across a BaSi2pn junction by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2015, 54, 030306.	1.5	5
134	Local electronic states of Fe4N films revealed by x-ray absorption spectroscopy and x-ray magnetic circular dichroism. Journal of Applied Physics, 2015, 117, .	2.5	18
135	Vertically Aligned Ge Nanowires on Flexible Plastic Films Synthesized by (111)-Oriented Ge Seeded Vaporâ€“Liquidâ€“Solid Growth. ACS Applied Materials & Interfaces, 2015, 7, 18120-18124.	8.0	21
136	Effects of flexible substrate thickness on Al-induced crystallization of amorphous Ge thin films. Thin Solid Films, 2015, 583, 221-225.	1.8	9
137	70â€‰Â°C synthesis of high-Sn content (25%) GeSn on insulator by Sn-induced crystallization of amorphous Ge. Applied Physics Letters, 2015, 106, .	3.3	64
138	MÃ¶ssbauer study on epitaxial CoxFe4â^'xN films grown by molecular beam epitaxy. Journal of Applied Physics, 2015, 117, .	2.5	7
139	Effect of Diffusion Control Layer on Reverse Al-Induced Layer Exchange Process for High-Quality Ge/Al/Glass Structure. Journal of Electronic Materials, 2015, 44, 1377-1381.	2.2	1
140	Formation of BaSi2 heterojunction solar cells using transparent MoOx hole transport layers. Applied Physics Letters, 2015, 106, .	3.3	19
141	Fabrication and characterization of BaSi₂ epitaxial films over 1 Âµm in thickness on Si(111). Japanese Journal of Applied Physics, 2014, 53, 04ER04.	1.5	31
142	Electrical and optical characterizations of an n-BaSi<inf>2</inf>/p-Si hetero-junction for solar cell applications. , 2014, , .		0
143	Grain boundaries characterization of semiconducting BaSi<inf>2</inf> thin films on a polycrystalline Si substrate. , 2014, , .		0
144	Potential variation around grain boundaries in BaSi2 films grown on multicrystalline silicon evaluated using Kelvin probe force microscopy. Journal of Applied Physics, 2014, 116, .	2.5	8

#	Article	IF	Citations
145	Low-temperature (180â€‰Â°C) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. Applied Physics Letters, 2014, 104, .	3.3	96
146	Engineering of p-n junction for high efficiency semiconducting BaSi2 based thin film solar cells. , 2014, , .		0
147	Photoresponse properties of undoped BaSi₂epitaxial layers on n⁺-BaSi₂/p⁺-Si(001) by molecular beam epitaxy. Japanese Journal of Applied Physics, 2014, 53, 058007.	1.5	16
148	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. Journal of Applied Physics, 2014, 115, .	2.5	40
149	Sign of the spin-polarization in cobalt-iron nitride films determined by the anisotropic magnetoresistance effect. Journal of Applied Physics, 2014, 116, .	2.5	39
150	Perpendicular magnetic anisotropy of Mn4N films on MgO(001) and SrTiO3(001) substrates. Journal of Applied Physics, 2014, 115, .	2.5	77
151	Al-induced crystallization of amorphous Ge thin films on conducting layer coated glass substrates. Japanese Journal of Applied Physics, 2014, 53, 04EH01.	1.5	7
152	Structural characterization of polycrystalline Ge thin films on insulators formed by diffusion-enhanced Al-induced layer exchange. Japanese Journal of Applied Physics, 2014, 53, 04EH03.	1.5	7
153	X-ray magnetic circular dichroism for Co_xFe_{4â^'}_xN (xâ€‰=â€‰0, 3, 4) films grown by molecular beam epitaxy. Journal of Applied Physics, 2014, 115, 17C712.	2.5	19
154	Potential variations around grain boundaries in impurity-doped BaSi2 epitaxial films evaluated by Kelvin probe force microscopy. Journal of Applied Physics, 2014, 116, .	2.5	23
155	Diffusion coefficients of impurity atoms in BaSi2epitaxial films grown by molecular beam epitaxy. Japanese Journal of Applied Physics, 2014, 53, 04ER02.	1.5	9
156	Influence of grain size and surface condition on minority-carrier lifetime in undoped n-BaSi2 on Si(111). Journal of Applied Physics, 2014, 115, .	2.5	80
157	N-type doping of BaSi2 epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. Thin Solid Films, 2014, 567, 105-108.	1.8	22
158	Si-based new material for high-efficiency thin film solar cells. , 2014, , .		0
159	Direct synthesis of highly textured Ge on flexible polyimide films by metal-induced crystallization. Applied Physics Letters, 2014, 104, .	3.3	20
160	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. CrystEngComm, 2014, 16, 2578.	2.6	17
161	Self-organization of Ge(111)/Al/glass structures through layer exchange in metal-induced crystallization. CrystEngComm, 2014, 16, 9590-9595.	2.6	10
162	Coherent lateral-growth of Ge over insulating film by rapid-melting-crystallization. Thin Solid Films, 2014, 557, 135-138.	1.8	1

#	Article	IF	Citations
163	Precipitation control and activation enhancement in boron-doped p+-BaSi2 films grown by molecular beam epitaxy. Applied Physics Letters, 2014, 104, .	3.3	32
164	Analysis of the electrical properties of Cr/n-BaSi2 Schottky junction and n-BaSi2/p-Si heterojunction diodes for solar cell applications. Journal of Applied Physics, 2014, 115, .	2.5	49
165	Evaluation of minority carrier diffusion length of undoped n-BaSi₂epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. Japanese Journal of Applied Physics, 2014, 53, 078004.	1.5	20
166	Growth promotion of Al-induced crystallized Ge films on insulators by insertion of a Ge membrane below the Al layer. Thin Solid Films, 2014, 557, 143-146.	1.8	16
167	Large-grained (111)-oriented Si/Al/SiO2 structures formed by diffusion-controlled Al-induced layer exchange. Thin Solid Films, 2014, 557, 147-150.	1.8	7
168	N-type doping of BaSi2 epitaxial films by phosphorus ion implantation and thermal annealing. Thin Solid Films, 2014, 557, 90-93.	1.8	26
169	Temperature dependent Al-induced crystallization of amorphous Ge thin films on SiO2 substrates. Journal of Crystal Growth, 2013, 372, 189-192.	1.5	16
170	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. Crystal Growth and Design, 2013, 13, 1767-1770.	3.0	44
171	Lattice and grain-boundary diffusions of boron atoms in BaSi2 epitaxial films on Si(111). Journal of Applied Physics, 2013, 113, .	2.5	21
172	In-situ heavily p-type doping of over 1020â€‰cmâ^'3 in semiconducting BaSi2 thin films for solar cells applications. Applied Physics Letters, 2013, 102, .	3.3	72
173	Effect of atomic-hydrogen irradiation on reduction of residual carrier concentration in Î²-FeSi2 films grown on Si substrates by atomic-hydrogen-assisted molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 365-367.	1.5	2
174	Characterization of grain boundary properties in BaSi2 epitaxial films on Si(111) and Si(001) by Kelvin probe force microscopy. , 2013, , .		0
175	Improvement of excess-carrier lifetime in BaSi<inf>2</inf> epitaxial films by post-growth annealing. , 2013, , .		0
176	Evaluation of diffusion coefficients of nâ€type impurities in MBEâ€grown BaSi₂ epitaxial layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1762-1764.	0.8	3
177	Molecular beam epitaxy of boron doped p-type BaSi2 epitaxial films on Si(111) substrates for thin-film solar cells. Journal of Crystal Growth, 2013, 378, 201-204.	1.5	18
178	Structural study on phosphorus doping of BaSi2 epitaxial films by ion implantation. Thin Solid Films, 2013, 534, 470-473.	1.8	15
179	Formation of polycrystalline BaSi2 films by radio-frequency magnetron sputtering for thin-film solar cell applications. Thin Solid Films, 2013, 534, 116-119.	1.8	32
180	Formation of large-grain-sized BaSi2 epitaxial layers grown on Si(111) by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 193-197.	1.5	5

#	Article	IF	Citations
181	Epitaxial growth of ferromagnetic CoxFe4â^'xN thin films on SrTiO3 (001) and magneticproperties. Journal of Crystal Growth, 2013, 378, 342-346.	1.5	5
182	Low-temperature crystallization of amorphous silicon and amorphous germanium by soft X-ray irradiation. Thin Solid Films, 2013, 534, 334-340.	1.8	16
183	Lattice and grain-boundary diffusions of impurity atoms in BaSi2 epitaxial layers grown by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 189-192.	1.5	9
184	Large photoresponsivity in semiconducting BaSi2 epitaxial films grown on Si(001) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 198-200.	1.5	4
185	Double-Layered Ge Thin Films on Insulators Formed by an Al-Induced Layer-Exchange Process. Crystal Growth and Design, 2013, 13, 3908-3912.	3.0	17
186	High-quality formation of multiply stacked SiGe-on-insulator structures by temperature-modulated successive rapid-melting-growth. Applied Physics Letters, 2013, 102, .	3.3	13
187	Large-Grained Polycrystalline (111) Ge Films on Insulators by Thickness-Controlled Al-Induced Crystallization. ECS Journal of Solid State Science and Technology, 2013, 2, Q195-Q199.	1.8	17
188	Atomically-Coherent-Coalescence of Two Growth-Fronts in Ge Stripes on Insulator by Rapid-Melting Lateral-Crystallization. ECS Journal of Solid State Science and Technology, 2013, 2, P54-P57.	1.8	1
189	(Invited) Hybrid-Formation of Ge-on-Insulator Structures on Si Platform by SiGe-Mixing-Triggered Rapid-Melting Growth --- A Road to Artificial Crystal ---. ECS Transactions, 2013, 50, 59-70.	0.5	0
190	Enhanced p-type conductivity and band gap narrowing in heavily B-doped p-BaSi<inf>2</inf> films grown by molecular beam epitaxy. , 2013, , .		0
191	Electronic structures and magnetic moments of Co3FeN thin films grown by molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	11
192	Evaluation of potential variations around grain boundaries in BaSi2 epitaxial films by Kelvin probe force microscopy. Applied Physics Letters, 2013, 103, .	3.3	29
193	Mechanism of strain relaxation in BaSi₂ epitaxial films on Si(111) substrates during postâ€growth annealing and application for film exfoliation. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1677-1680.	0.8	16
194	Determination of Bulk Minority-Carrier Lifetime in BaSi₂Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. Applied Physics Express, 2013, 6, 112302.	2.4	75
195	Fabrication and characterizations of phosphorusâ€doped nâ€type BaSi₂ epitaxial films grown by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1753-1755.	0.8	15
196	Hard x-ray photoelectron spectroscopy study on valence band structure of semiconducting BaSi2. Journal of Applied Physics, 2013, 114, 123702.	2.5	15
197	Investigation of the tunneling properties and surface morphologies of BaSi2 /Si tunnel junctions for BaSi2 solar cell applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1765-1768.	0.8	1
198	Effect of Ge/Al thickness on Al-induced crystallization of amorphous Ge layers on glass substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1781-1784.	0.8	0

#	Article	IF	Citations
199	Fabrication of n⁺â€BaSi₂/p⁺â€Si tunnel junction on Si(001) surface for characterization of photoresponse properties of BaSi₂epitaxial films. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1773-1776.	0.8	0
200	Fabrication of BaSi2 films on (111)-oriented Si layers formed by inverted Al-induced crystallization method on glass structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1769-1772.	0.8	1
201	Epitaxial growth of BaSi2films with large grains using vicinal Si(111) substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1756-1758.	0.8	1
202	Fabrication and characterization of polycrystalline BaSi₂ by RF sputtering. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1759-1761.	0.8	45
203	Negative spin polarization at the Fermi level in Fe4N epitaxial films by spin-resolved photoelectron spectroscopy. Journal of Applied Physics, 2012, 112, .	2.5	27
204	Realization of Large-Domain Barium Disilicide Epitaxial Thin Film by Introduction of Miscut to Si(111) Substrate. Japanese Journal of Applied Physics, 2012, 51, 10NB06.	1.5	2
205	Negative Anisotropic Magnetoresistance in Î³'-Fe₄N Epitaxial Films on SrTiO₃(001) Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 068001.	1.5	17
206	Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n⁺-BaSi₂/p⁺-Si Tunnel Junction to Undoped BaSi₂ Overlayers. Japanese Journal of Applied Physics, 2012, 51, 04DP01.	1.5	1
207	Epitaxy of Orthorhombic BaSi$_{2}$ with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. Japanese Journal of Applied Physics, 2012, 51, 095501.	1.5	15
208	Molecular Beam Epitaxy of BaSi$_{2}$ Films with Grain Size over 4 mum on Si(111). Japanese Journal of Applied Physics, 2012, 51, 098003.	1.5	18
209	Crystallization mechanism of thick a-Si<inf>0.5</inf>Ge<inf>0.5</inf> film by excimer laser annealing. , 2012, , .		0
210	Electrical characterization and conduction mechanism of impurity-doped BaSi2 films grown on Si(111) by molecular beam epitaxy. Thin Solid Films, 2012, 522, 95-99.	1.8	45
211	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. Applied Physics Letters, 2012, 101, 072106.	3.3	88
212	Improved internal quantum efficiency in high-quality BaSi<inf>2</inf> films grown by molecular beam epitaxy. , 2012, , .		0
213	Investigation of the carrier recombination process in undoped barium disilicide epitaxial films. , 2012, , .		0
214	Molecular beam epitaxy of BaSi2 thin films on Si(001) substrates. Journal of Crystal Growth, 2012, 345, 16-21.	1.5	61
215	Investigation of grain boundaries in BaSi2 epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. Journal of Crystal Growth, 2012, 348, 75-79.	1.5	133
216	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO2 insertion layer thickness. Journal of Crystal Growth, 2012, 356, 65-69.	1.5	21

#	Article	IF	Citations
217	Molecular beam epitaxy of Co Fe4â^'N (0.4<x<2.9) thin films on SrTiO3(001) substrates. Journal of Crystal Growth, 2012, 357, 53-57.	1.5	13
218	Rotational and vibrational temperatures in a hydrogen discharge with a magnetic X-point. Physics of Plasmas, 2012, 19, 123503.	1.9	13
219	Nano-lithography free formation of high density Ge-on-insulator network for epitaxial template. Applied Physics Letters, 2012, 100, 092111.	3.3	5
220	Improved photoresponsivity of semiconducting BaSi₂ epitaxial films grown on a tunnel junction for thin-film solar cells. Applied Physics Letters, 2012, 100, 152114.	3.3	50
221	Investigation of the recombination mechanism of excess carriers in undoped BaSi2 films on silicon. Journal of Applied Physics, 2012, 112, .	2.5	84
222	Effect of Solid-Phase-Epitaxy Si Layers on Suppression of Sb Diffusion from Sb-Doped n⁺-BaSi₂/p⁺-Si Tunnel Junction to Undoped BaSi₂Overlayers. Japanese Journal of Applied Physics, 2012, 51, 04DP01.	1.5	1
223	Negative Anisotropic Magnetoresistance in Î³'-Fe₄N Epitaxial Films on SrTiO₃(001) Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 068001.	1.5	9
224	Epitaxy of Orthorhombic BaSi2with Preferential In-Plane Crystal Orientation on Si(001): Effects of Vicinal Substrate and Annealing Temperature. Japanese Journal of Applied Physics, 2012, 51, 095501.	1.5	2
225	Molecular Beam Epitaxy of BaSi2Films with Grain Size over 4 Âµm on Si(111). Japanese Journal of Applied Physics, 2012, 51, 098003.	1.5	2
226	Epitaxial growth and magnetic characterization of ferromagnetic Co4N thin films on SrTiO3(001) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2011, 336, 40-43.	1.5	35
227	Growth-Direction Dependent Rapid-Melting-Growth of Ge-On-Insulator (GOI) and its Application to Ge Mesh-Growth. ECS Transactions, 2011, 35, 55-60.	0.5	2
228	Al-Induced oriented-crystallization of Si films on quartz and its application to epitaxial template for Ge growth. Solid-State Electronics, 2011, 60, 7-12.	1.4	29
229	Strained single-crystal GOI (Ge on Insulator) arrays by rapid-melting growth from Si (111) micro-seeds. Solid-State Electronics, 2011, 60, 22-25.	1.4	1
230	Growth-direction-dependent characteristics of Ge-on-insulator by Siâ€“Ge mixing triggered melting growth. Solid-State Electronics, 2011, 60, 18-21.	1.4	2
231	Chip-size formation of high-mobility Ge strips on SiN films by cooling rate controlled rapid-melting growth. Applied Physics Letters, 2011, 99, 032103.	3.3	47
232	X-ray magnetic circular dichroism of ferromagnetic Co4N epitaxial films on SrTiO3(001) substrates grown by molecular beam epitaxy. Applied Physics Letters, 2011, 99, 252501.	3.3	23
233	Single-crystalline (100) Ge networks on insulators by rapid-melting growth along hexagonal mesh-pattern. Applied Physics Letters, 2011, 98, .	3.3	21
234	Mesh-shape-and-size controlled rapid-melting growth for the formation of single-crystalline (100), (110), and (111) Ge networks on insulators. Applied Physics Letters, 2011, 98, .	3.3	15

#	Article	IF	Citations
235	SiGe-Mixing-Triggered Rapid-Melting-Growth of High-Mobility Ge-On-Insulator. Key Engineering Materials, 2011, 470, 8-13.	0.4	5
236	Low-Temperature (â^¼â€‰250Â°C) Cu-Induced Lateral Crystallization of Amorphous Ge on Insulator. Electrochemical and Solid-State Letters, 2011, 14, H274.	2.2	33
237	Structural Study of BF₂ Ion Implantation and Post Annealing of BaSi₂ Epitaxial Films. Japanese Journal of Applied Physics, 2011, 50, 121202.	1.5	11
238	Structural Study of BF2Ion Implantation and Post Annealing of BaSi2Epitaxial Films. Japanese Journal of Applied Physics, 2011, 50, 121202.	1.5	2
239	(100) Orientation-Controlled Ge Giant-Stripes on Insulating Substrates by Rapid-Melting Growth Combined with Si Micro-Seed Technique. Applied Physics Express, 2010, 3, 075603.	2.4	19
240	Formation of single-crystalline Ge stripes on quartz substrates by SiGe mixing-triggered liquid-phase epitaxy. Thin Solid Films, 2010, 518, S179-S181.	1.8	4
241	Liquid-phase epitaxial growth of Ge island on insulator using Ni-imprint-induced Si crystal as seed. Thin Solid Films, 2010, 518, S182-S185.	1.8	0
242	High Quality Single-Crystalline Ge-Rich SiGe on Insulator Structures by Si-Doping Controlled Rapid Melting Growth. Applied Physics Express, 2010, 3, 031301.	2.4	21
243	High-mobility defect-free ge single-crystals by rapid melting growth on insulating substrates. , 2010, , .		0
244	Defect-free Ge-on-insulator with (100), (110), and (111) orientations by growth-direction-selected rapid-melting growth. Applied Physics Letters, 2010, 97, .	3.3	21
245	High-Hole-Mobility Single-Crystalline Ge Thin Films Formed on Insulating Substrates by SiGe Mixing-Triggered Directional Melting Growth. Japanese Journal of Applied Physics, 2010, 49, 04DA08.	1.5	5
246	Defect-free single-crystal Ge island arrays on insulator by rapid-melting-growth combined with seed-positioning technique. Applied Physics Letters, 2009, 95, 112107.	3.3	24
247	High-quality single-crystal Ge stripes on quartz substrate by rapid-melting-growth. Applied Physics Letters, 2009, 95, .	3.3	75
248	Indentation-induced low-temperature solid-phase crystallization of Si1â^'xGexâ€^(x=â€“1) on insulator. Applied Physics Letters, 2009, 94, .	3.3	20
249	Formation of SiGe Quasi-Single Crystal Grain on Insulator by Indentation-Induced Solid-Phase Crystallization. ECS Transactions, 2009, 16, 219-222.	0.5	0
250	Position-Controlled Growth of SiGe Crystal Grains on Insulator by Indentation-Induced Solid-Phase Crystallization. Japanese Journal of Applied Physics, 2009, 48, 03B007.	1.5	2
251	Electrical properties of poly-Ge on glass substrate grown by two-step solid-phase crystallization. Solid-State Electronics, 2009, 53, 1159-1164.	1.4	137
252	Low-temperature solid-phase crystallization of amorphous SiGe films on glass by imprint technique. Solid-State Electronics, 2008, 52, 1221-1224.	1.4	2

#	Article	IF	Citations
253	Nucleation-Controlled Metal-Induced Lateral Crystallization of Amorphous Si1-xGexwith Whole Ge Fraction on Insulator. Japanese Journal of Applied Physics, 2008, 47, 1876-1879.	1.5	8
254	Ni-imprint induced solid-phase crystallization in Si1â^'xGex (x: 0â€“1) on insulator. Applied Physics Letters, 2007, 91, .	3.3	60
255	Temperature dependent metal-induced lateral crystallization of amorphous SiGe on insulating substrate. Applied Physics Letters, 2006, 89, 182120.	3.3	73
256	Multichannel taste sensor using electric potential changes in lipid membranes. Biosensors and Bioelectronics, 1994, 9, 359-364.	10.1	81
257	Electrical characteristics in an excitable element of lipid membrane. Biophysical Chemistry, 1991, 41, 143-156.	2.8	6
258	Flux creep and irreversibility line in highâ€temperature oxide superconductors. Applied Physics Letters, 1990, 56, 2039-2041.	3.3	120
259	Oscillations of electrical potential along a root of a higher plant. Biophysical Journal, 1990, 57, 269-279.	0.5	32
260	Growth and electric current loops in plants. Biophysical Chemistry, 1989, 33, 161-176.	2.8	20
261	Spontaneous formation of the spatial pattern of electric potential in biological systems. Ferroelectrics, 1988, 86, 269-279.	0.6	10
262	Relation of growth process to spatial patterns of electric potential and enzyme activity in bean roots. Biophysical Chemistry, 1987, 27, 39-58.	2.8	35
263	Theory of electric dissipative structure in Characean internode. Biophysical Chemistry, 1987, 27, 149-172.	2.8	5
264	Dynamic property of membrane formation in a protoplasmic droplet of nitella. Biophysical Chemistry, 1985, 21, 295-313.	2.8	9
265	On the oscillatory phenomenon in an oil/water interface. Biophysical Chemistry, 1985, 22, 151-158.	2.8	40
266	Current-voltage characteristics and self-sustained oscillations in dioleyl phosphate-millipore membranes. Biophysical Chemistry, 1984, 20, 39-59.	2.8	58
267	Stabilization effect of protons and divalent cations on membrane structures of lipids. Biophysical Chemistry, 1981, 14, 11-23.	2.8	32
268	Electronic sensing of the taste of beer and other foodstuffs. , 0, , .		3
269	Giant Ge-on-Insulator Formation by Siâ€“Ge Mixing-Triggered Liquid-Phase Epitaxy. Applied Physics Express, 0, 2, 045503.	2.4	87
270	Thermoelectric Inorganic SiGe Film Synthesized on Flexible Plastic Substrate. ACS Applied Energy Materials, 0, , .	5.1	26

#	Article	IF	Citations
271	Solidâ€phase crystallization of GeSn thin films on GeO 2 â€coated glass. Physica Status Solidi - Rapid Research Letters, 0, , 2100509.	2.4	3